

**N-Ch MOSFET** 

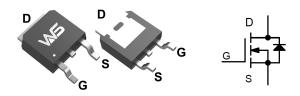
### Description

The uses advanced SGT technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## **Product Summery**

BVDSS	RDSON	ID
100V	<b>13.8m</b> Ω	40A

# **TO-252 Pin Configuration**



## Application

Consumer electronic power supply Motor control Synchronous-rectification Isolated DC

# Absolute Maximum Ratings (TC=25°Cunless otherwise noted)

Symbol	Parameter		Rating	Units
VDS	Drain source voltage		100	V
VGS	Gate source voltage		±20	V
ID	Continuous drain current1)	<b>TC=25</b> ℃	40	A
ID, pulse	Pulsed drain current <sub>2)</sub>	<b>TC=25</b> ℃	120	А
Po	Power dissipation <sub>3)</sub>	<b>TC=25</b> ℃	71	W
EAS	Single pulsed avalanche energy <sub>5)</sub>		57	mJ
Tstg, Tj	Operation and storage temperature		-55 to 150	°C
RθJC	Thermal resistance, junction-case		1.76	°C/W
RθJA	Thermal resistance, junction-ambient4)		62	°C/W



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#### Electrical Characteristics (Tc=25°C unless otherwise noted)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
BVDSS	Drain-source breakdown voltage	Vgs=0 V, Ισ=250 μΑ	100	107	-	V
VGS(th)	Gate threshold voltage	Vos=Vgs, Io=250 µA	1.2	1.5	2.5	V
RDS(ON)	Drain-source on-state resistance	Vgs=10 V, Id=10 A	-	13.8	20.0	mΩ
RDS(ON)	Drain-source on-state resistance	Vgs=4.5 V, Id=7 A	-	17.4	26.0	mΩ
IGSS	Gate-source leakage current	V <sub>GS</sub> =±20 V	-	-	±100	nA
IDSS	Drain-source leakage current	VDS=100 V, VGS=0 V	-	-	1	uA
Ciss	Input capacitance	V <sub>GS</sub> =0 V, V <sub>DS</sub> =50 V, f=100 kHz	-	1003.9	-	pF
Coss	Output capacitance		-	185.4	-	pF
Crss	Reverse transfer capacitance		-	9.8	-	pF
td(on)	Turn-on delay time	Vgs=10 V, Vds=50 V, Rg=10 Ω, Id=5 A	-	16.6	-	ns
tr	Rise time		-	3.8	-	ns
td(off)	Turn-off delay time		-	75.5	-	ns
tr	Fall time		-	46	-	ns
Qg	Total gate charge	ID=5 A, VDS=50V, VGS=10V	-	16.2	-	nc
Qgs	Gate-source charge		-	2.8	-	nc
Qgd	Gate-drain charge		-	4.1	-	nc
Vplateau	Gate plateau voltage		-	3	-	V
ls	Diode forward current		-	30	-	А
ISP	Pulsed source current		-	90	-	А
trr	Reverse recovery time	Is=1A, di/dt=100 A/µs	49	-	-	ns
Qrr	Reverse recovery charge		61.8	-	-	nc
Irrm	Peak reverse recovery current		2.4	-	-	А

#### Note :

1. Calculated continuous current based on maximum allowable junction temperature.

- 2. Repetitive rating; pulse width limited by max. junction temperature.
- $3\,{}_{\!\scriptscriptstyle \rm C}$  Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4. The value of  $R_{\text{O}ja}$  is measured with the device mounted on 1 in 2 FR-4 board

with 2oz. Copper, in a still air environment with Ta=25 °C.

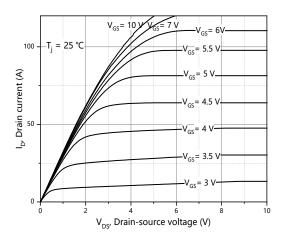
5、VDD=50 V, RG=25  $\Omega$ , L=0.3 mH, starting Tj=25 °C.

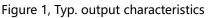


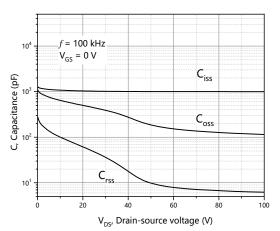
**WSF50N10G** 

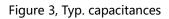
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## **Typical Characteristics**









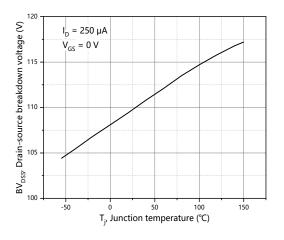


Figure 5, Drain-source breakdown voltage

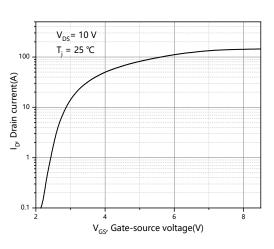


Figure 2, Typ. transfer characteristics

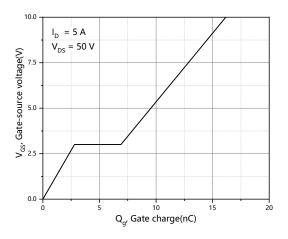


Figure 4, Typ. gate charge

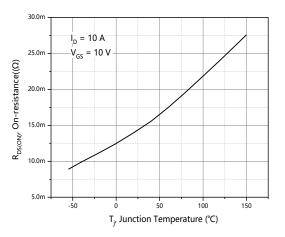
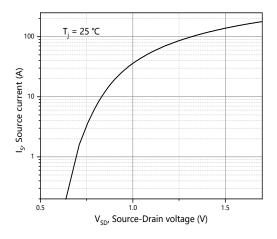


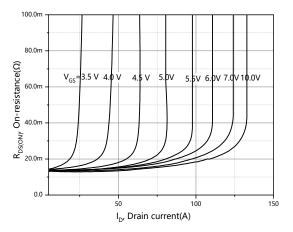
Figure 6, Drain-source on-state resistance





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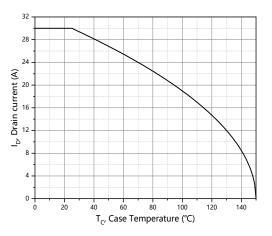




Figure 8, Drain-source on-state resistance

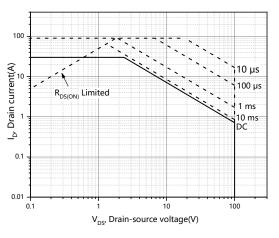
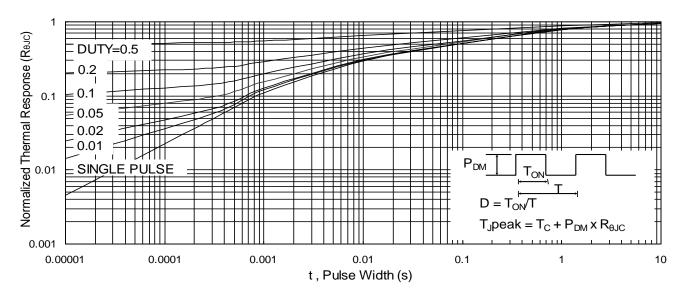


Figure 10, Safe operation area  $T_C=25$  °C



Figu11. Normalized Maximum Transient Thermal Impedance



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